

# Xiao-Guang Yang

## List of Publications by Year in descending order

Source: <https://exaly.com/author-pdf/8265744/publications.pdf>

Version: 2024-02-01

26  
papers

337  
citations

1163117

8  
h-index

839539

18  
g-index

26  
all docs

26  
docs citations

26  
times ranked

501  
citing authors

#	ARTICLE	IF	CITATIONS
1	A-axis oriented Zn <sub>0.72</sub> Mg <sub>0.28</sub> O epitaxial thin films with large second-order nonlinear susceptibility. <i>Journal Physics D: Applied Physics</i> , 2022, 55, 19LT01.	2.8	3
2	Optically Rough and Physically Flat Transparent Conductive Substrates with Strong Far-Field Scattering. <i>ACS Applied Materials &amp; Interfaces</i> , 2022, 14, 12893-12900.	8.0	0
3	Detailed Balance-Limiting Efficiency of Solar Cells with Dual Intermediate Bands Based on InAs/InGaAs Quantum Dots. <i>Photonics</i> , 2022, 9, 290.	2.0	3
4	Significantly improved performances of 1.3- $\mu\text{m}$ InAs/GaAs QD laser by spatially separated dual-doping. <i>Applied Physics Letters</i> , 2022, 121, .	3.3	3
5	Improved linewidth enhancement factor of 1.3- $\mu\text{m}$ InAs/GaAs quantum dot lasers by direct Si doping. <i>AIP Advances</i> , 2021, 11, 055002.	1.3	3
6	1.3 $\mu\text{m}$ p-Modulation Doped InGaAs/GaAs Quantum Dot Lasers with High Speed Direct Modulation Rate and Strong Optical Feedback Resistance. <i>Crystals</i> , 2020, 10, 980.	2.2	1
7	Enhanced performance of InAs/GaAs quantum dot superluminescent diodes by direct Si-doping. <i>AIP Advances</i> , 2020, 10, 045202.	1.3	4
8	25 Gb/s directly modulated ground-state operation of 1.3 $\mu\text{m}$ InAs/GaAs quantum dot lasers up to 75 $^{\circ}\text{C}$ . <i>Chinese Optics Letters</i> , 2020, 18, 071401.	2.9	3
9	Multibit Optoelectronic Memory in Topâ€Floatingâ€Gated van der Waals Heterostructures. <i>Advanced Functional Materials</i> , 2019, 29, 1902890.	14.9	69
10	Surface Modification of Al-Doped ZnO Transparent Conductive Thin Films with Polycrystalline Zinc Molybdenum Oxide. <i>ACS Applied Materials &amp; Interfaces</i> , 2019, 11, 26491-26499.	8.0	10
11	Self-Seeded MOCVD Growth and Dramatically Enhanced Photoluminescence of InGaAs/InP Coreâ€Shell Nanowires. <i>Nanoscale Research Letters</i> , 2018, 13, 269.	5.7	5
12	Improved performance of 1.3- $\mu\text{m}$ InAs/GaAs quantum dot lasers by direct Si doping. <i>Applied Physics Letters</i> , 2018, 113, .	3.3	22
13	Self-Flattened ZnO:Al Transparent Conductive Thin Films Derived by Solâ€Gel Process. <i>IEEE Journal of Photovoltaics</i> , 2018, 8, 1149-1155.	2.5	7
14	Defect-free InAsSb nanowire arrays on Si substrates grown by selective-area metalâ€organic chemical vapor deposition. <i>Nanotechnology</i> , 2018, 29, 405601.	2.6	5
15	Influences of Ridge-Waveguide Shape and Width on Performances of InP-Based Coupled Ridge-Waveguide Laser Arrays. <i>IEEE Journal of Quantum Electronics</i> , 2018, 54, 1-4.	1.9	1
16	Self-Catalyzed Growth of Vertical GaSb Nanowires on InAs Stems by Metal-Organic Chemical Vapor Deposition. <i>Nanoscale Research Letters</i> , 2017, 12, 428.	5.7	7
17	2004-nm Ridge-Waveguide Distributed Feedback Lasers With InGaAs Multi-Quantum Wells. <i>IEEE Photonics Technology Letters</i> , 2016, 28, 2257-2260.	2.5	7
18	Selective-Area MOCVD Growth and Carrier-Transport-Type Control of InAs(Sb)/GaSb Coreâ€Shell Nanowires. <i>Nano Letters</i> , 2016, 16, 7580-7587.	9.1	26

#	ARTICLE	IF	CITATIONS
19	Large Signal Modulation Characteristics in the Transition Regime for Two-State Lasing Quantum Dot Lasers. Chinese Physics Letters, 2016, 33, 124204.	3.3	3
20	Flat-topped ultrabroad stimulated emission from chirped InAs/InP quantum dot laser with spectral width of 92â€%nm. Applied Physics Letters, 2016, 108, .	3.3	5
21	Controlled-Direction Growth of Planar InAsSb Nanowires on Si Substrates without Foreign Catalysts. Nano Letters, 2016, 16, 877-882.	9.1	29
22	The self-seeded growth of InAsSb nanowires on silicon by metal-organic vapor phase epitaxy. Journal of Crystal Growth, 2014, 396, 33-37.	1.5	32
23	Optimizing the double-cap procedure for InAs/InGaAsP/InP quantum dots by metal-organic chemical vapor deposition. , 2013, , .		0
24	Improved efficiency of InAs/GaAs quantum dots solar cells by Si-doping. Solar Energy Materials and Solar Cells, 2013, 113, 144-147.	6.2	66
25	Impact of double-cap procedure on the characteristics of InAs/InGaAsP/InP quantum dots grown by metal-organic chemical vapor deposition. Journal of Crystal Growth, 2013, 375, 100-103.	1.5	15
26	Si delta doping inside InAs/GaAs quantum dots with different doping densities. Journal of Vacuum Science and Technology B:Nanotechnology and Microelectronics, 2012, 30, 041808.	1.2	8